

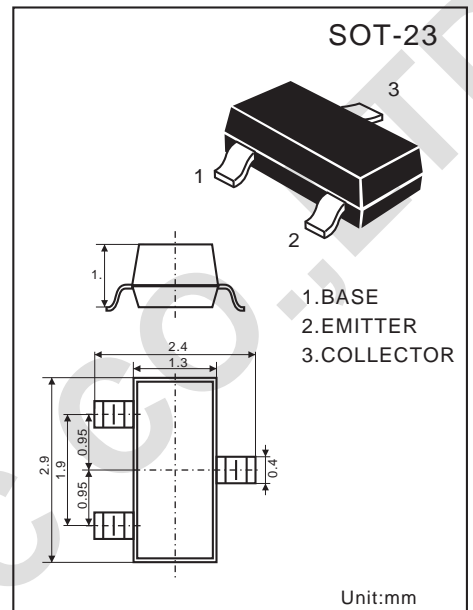
PNP SILICON TRANSISTOR

Features

- Power dissipation
 $P_{CM} : 0.3 \text{ W (Tamb=25}^\circ\text{C)}$
- Pluse Drain
 $I_{CM} : -0.1 \text{ mA}$
- Reverse Voltage
 $V_{(BR)CBO} : \text{BC856 } -80\text{V}$
 $\text{BC857 } -50\text{V}$
 $\text{BC858 } -30\text{V}$

Operating and storage junction temperature range

$$T_j, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$



Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BC856 BC857 BC858	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$		-80 -50 -30	V
Collector-Emitter Breakdown Voltage	BC856 BC857 BC858	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$		-65 -45 -30	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E = -1\mu\text{A}, I_C = 0$		-5	V
Collector Cut-off Current	BC856 BC857 BC858	I_{CBO}	$V_{CB} = -70\text{V}, I_E = 0$ $V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -25\text{V}, I_E = 0$		-0.1	μA
Collector Cut-off Current	BC856 BC857 BC858	I_{CEO}	$V_{CB} = -60\text{V}, I_E = 0$ $V_{CB} = -40\text{V}, I_E = 0$ $V_{CB} = -25\text{V}, I_E = 0$		-0.1	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-0.1	μA
DC Current Gain (Note)	BC856 BC857 BC858	$H_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	125 220 420	250 475 800	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-0.5	V
Base-emitter saturatio voltage		$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-1	V
Transition Frequency		f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	100		MHz

Typical Characteristics

